2MBI200NB-120-01

IGBT Module

1200V / 200A 2 in one-package

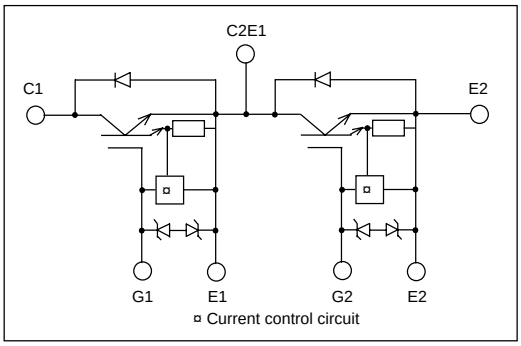
■ Features

· VCE(sat) classified for easy parallel connection
· High speed switching
· Voltage drive
· Low inductance module structure

■ Applications

· Inverter for Motor drive
· AC and DC Servo drive amplifier
· Uninterruptible power supply
· Industrial machines, such as Welding machines

■ Equivalent Circuit Schematic



■ Maximum ratings and characteristics

● **Absolute maximum ratings (at Tc=25°C unless otherwise specified)**

Item		Symbol	Rating	Unit
Collector-Emitter voltage		V_{CES}	1200	V
Gate-Emitter voltage		V_{GES}	±20	V
Collector current	Continuous	I_C	200	A
	1ms	I_C pulse	400	A
		-I_C	200	A
	1ms	-I_C pulse	400	A
Max. power dissipation		P_C	1500	W
Operating temperature		T_j	+150	°C
Storage temperature		T_{stg}	-40 to +125	°C
Isolation voltage		V_{is}	AC 2500 (1min.)	V
Screw torque		Mounting *1	3.5	N·m
		Terminals *2	4.5	N·m

*1 : Recommendable value : 2.5 to 3.5 N·m (M5) or (M6)
*2 : Recommendable value : 3.5 to 4.5 N·m (M6)

● **VCE(sat) classification**

Rank	Lenge	Conditions
F	2.25 to 2.50V	
A	2.40 to 2.65V	I_C = 200A
B	2.55 to 2.80V	V_{GE} = 15V
C	2.70 to 2.95V	Tj = 25°C
D	2.85 to 3.10V	
E	3.00 to 3.30V	

● **Electrical characteristics (at Tj=25°C unless otherwise specified)**

Item	Symbol	Characteristics			Conditions	Unit
		Min.	Typ.	Max.		
Zero gate voltage collector current	I_{CES}	–	–	2.0	V_{GE}=0V, V_{CE}=1200V	mA
Gate-Emitter leakage current	I_{GES}	–	–	30	V_{CE}=0V, V_{GE}=±20V	µA
Gate-Emitter threshold voltage	$V_{GE(th)}$	4.5	–	7.5	V_{CE}=20V, I_C=200mA	V
Collector-Emitter saturation voltage	$V_{CE(sat)}$	–	–	3.3	V_{GE}=15V, I_C=200A	V
Input capacitance	C_{ies}	–	32000	–	V_{GE}=0V	pF
Output capacitance	C_{oes}	–	11600	–	V_{CE}=10V	
Reverse transfer capacitance	C_{res}	–	10320	–	f=1MHz	
Turn-on time	t_{on}	–	0.65	1.2	V_{CC}=600V	µs
	t_r	–	0.25	0.6	I_C=200A	
Turn-off time	t_{off}	–	0.85	1.5	V_{GE}=±15V	
	t_f	–	0.35	0.5	R_G=4.7ohm	
Diode forward on voltage	V_F	–	–	3.0	I_F=200A, V_{GE}=0V	V
Reverse recovery time	t_{rr}	–	–	0.35	I_F=200A	µs

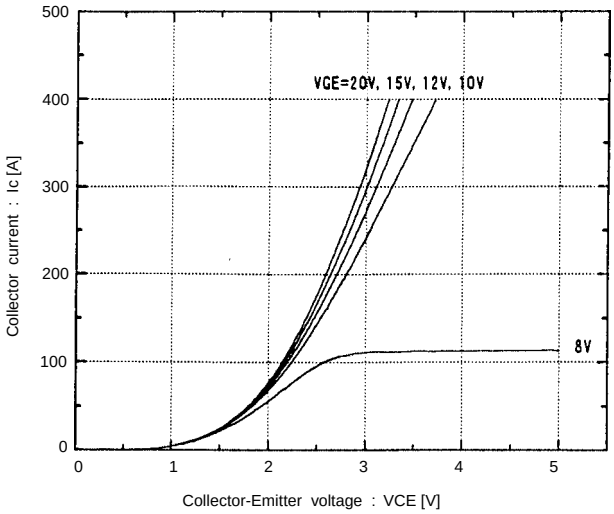
● **Thermal resistance characteristics**

Item	Symbol	Characteristics			Conditions	Unit
		Min.	Typ.	Max.		
Thermal resistance	Rth(j-c)	–	–	0.085	IGBT	°C/W
	Rth(j-c)	–	–	0.18	Diode	°C/W
	Rth(c-f)*	–	0.025	–	the base to cooling fin	°C/W

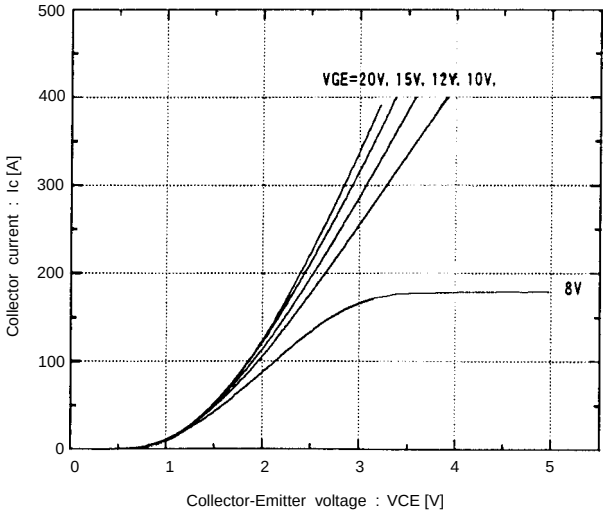
* : This is the value which is defined mounting on the additional cooling fin with thermal compound

■ Characteristics (Representative)

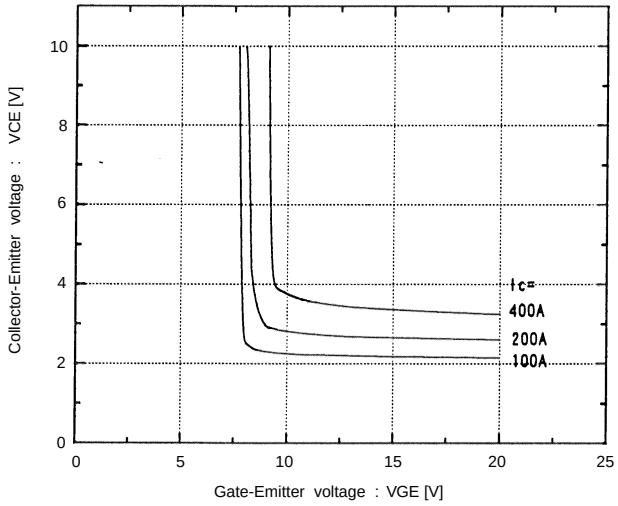
Collector current vs. Collector-Emitter voltage
Tj=25°C



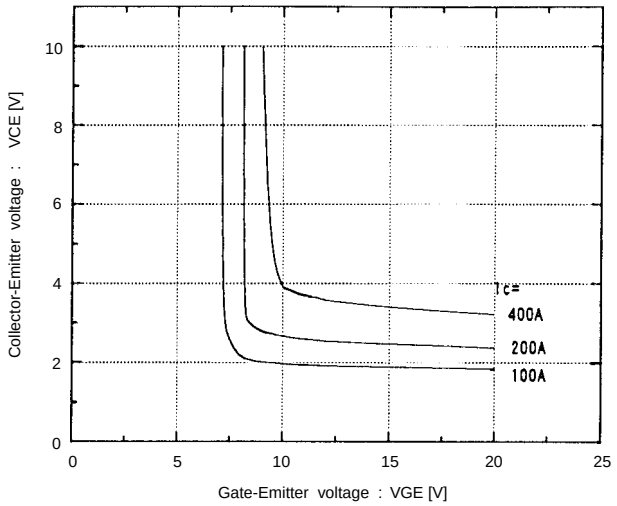
Collector current vs. Collector-Emitter voltage
Tj=125°C



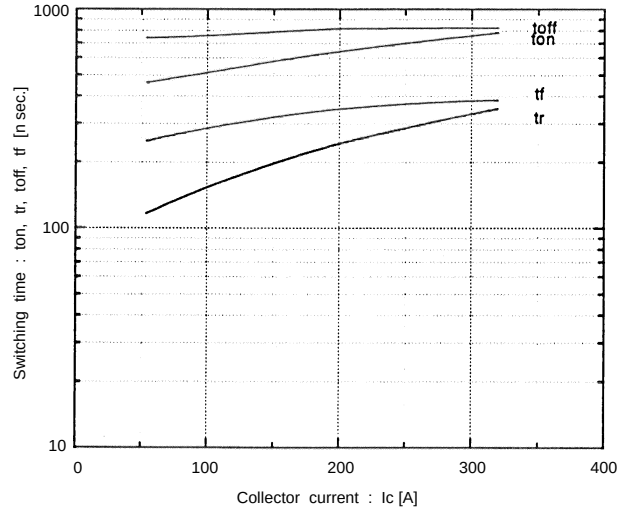
Collector-Emitter vs. Gate-Emitter voltage
Tj=25°C



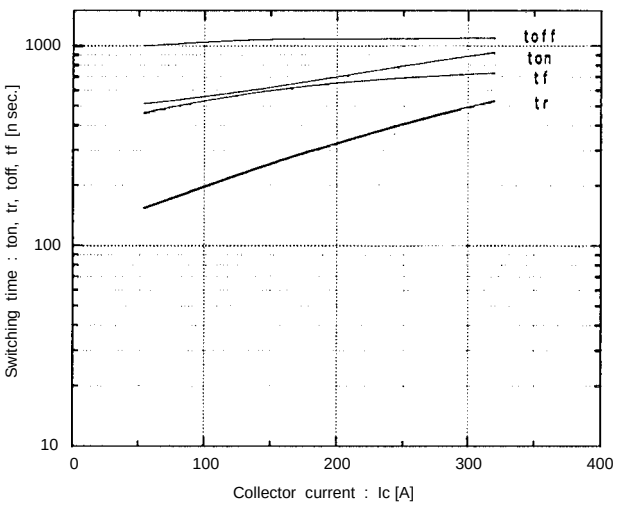
Collector-Emitter vs. Gate-Emitter voltage
Tj=125°C



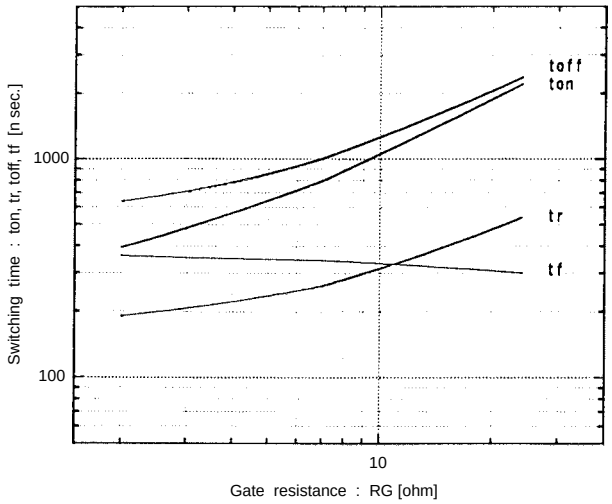
Switching time vs. Collector current
Vcc=600V, RG=4.7 ohm, VGE=±15V, Tj=25°C



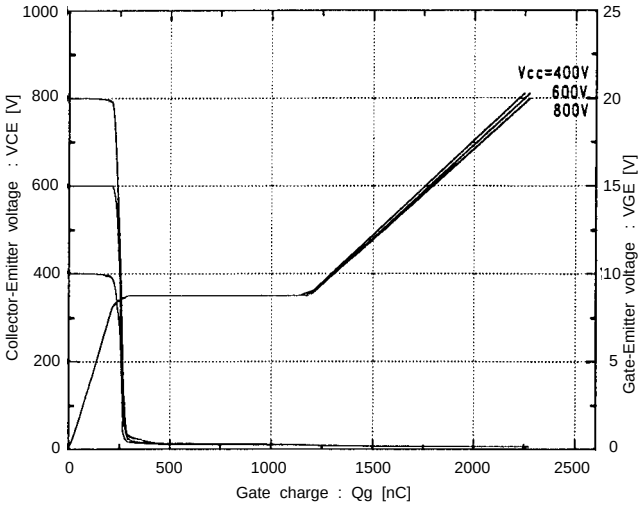
Switching time vs. Collector current
Vcc=600V, RG=4.7 ohm, VGE=±15V, Tj=125°C



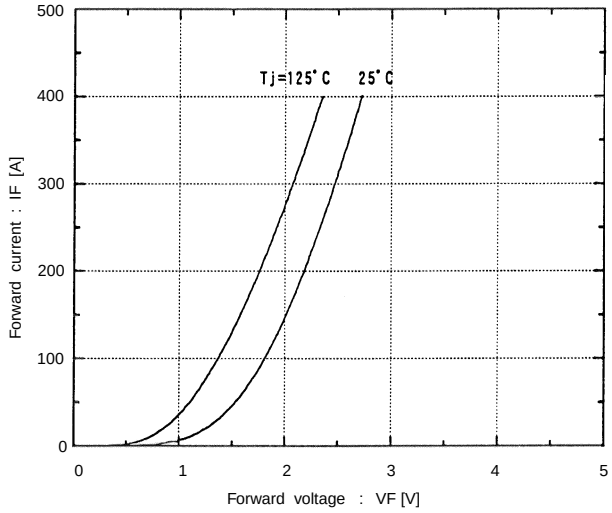
Switching time vs. RG
Vcc=600V, Ic=200A, VGE=±15V, Tj=25°C



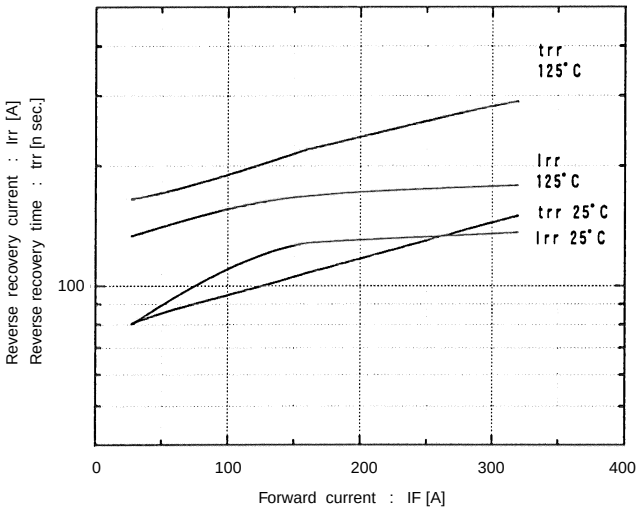
Dynamic input characteristics
Tj=25°C



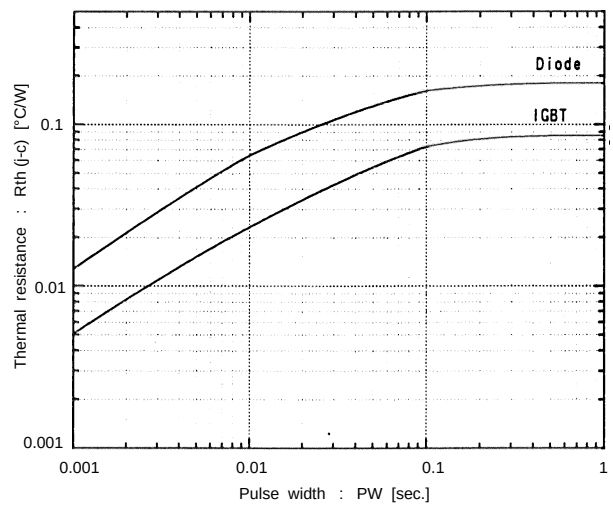
Forward current vs. Forward voltage
VGE=0V



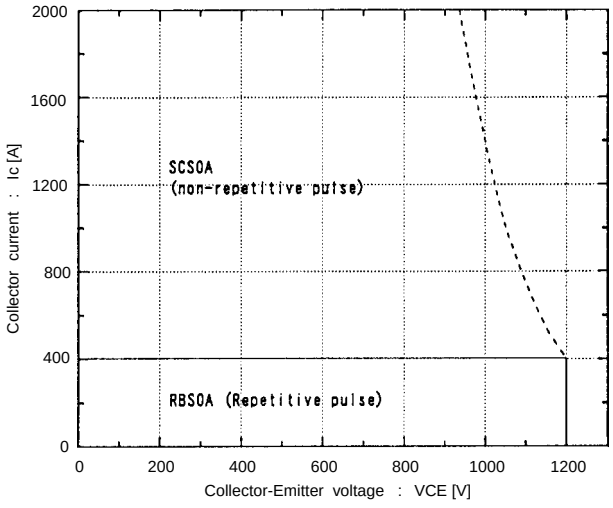
Reverse recovery characteristics
trr, Irr, vs. IF



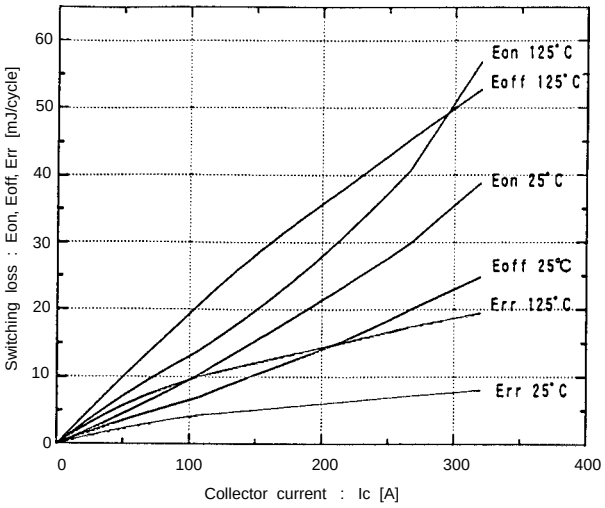
Transient thermal resistance



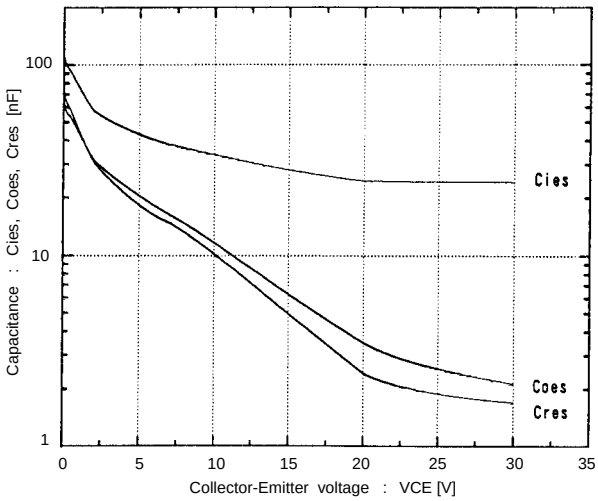
Reversed biased safe operating area
+VGE=15V, -VGE ≦ 15V, Tj ≦ 125°C, RG ≧ 4.7ohm



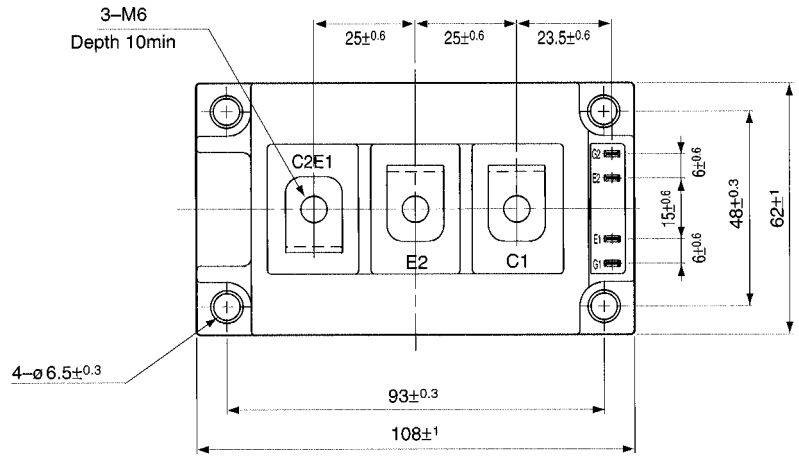
Switching loss vs. Collector current
Vcc=600V, RG=4.7 ohm, VGE=±15V

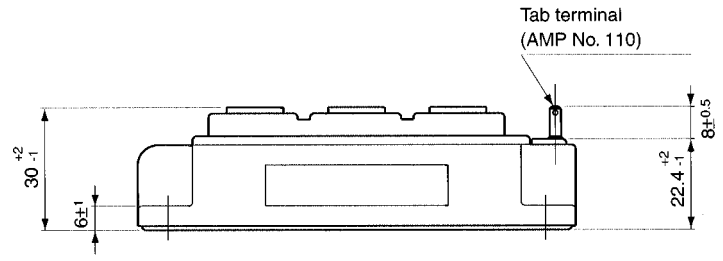


Capacitance vs. Collector-Emitter voltage
Tj=25°C



■ Outline Drawings, mm





Mass : 370g